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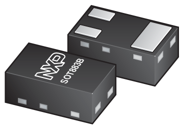


PMZB420UN

30 V, single N-channel Trench MOSFET

Rev. 1 — 11 May 2012 Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Fast switching
- Trench MOSFET technology
- Low threshold voltage
- Ultra thin package profile with 0.37 mm height

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

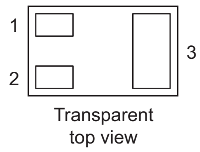
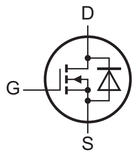
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage			-8	-	8	V
I_D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C	[1]	-	-	900	mA
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 200 mA; T_j = 25 °C		-	420	490	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm^2.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 SOT883B (DFN1006B-3)	 017aaa253
2	S	source		
3	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMZB420UN	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

4. Marking

Table 4. Marking codes

Type number	Marking code
PMZB420UN	0000 1010

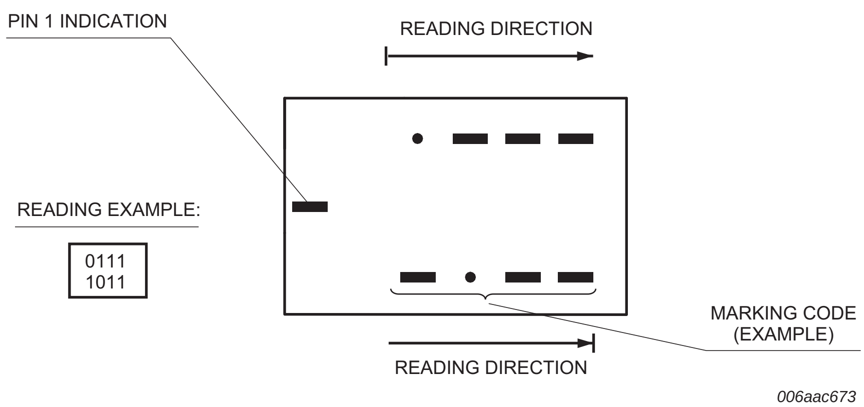


Fig 1. DFN1006B-3 (SOT883B) binary marking code description

5. Limiting values

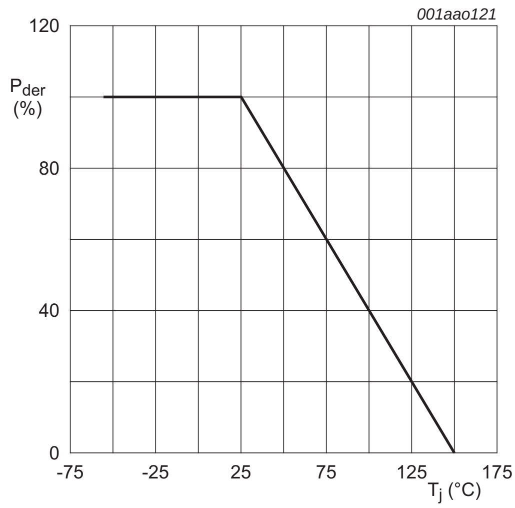
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	30	V
V_{GS}	gate-source voltage			-8	8	V
I_D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C	[1]	-	900	mA
		V_{GS} = 4.5 V; T_{amb} = 100 °C	[1]	-	570	mA
I_{DM}	peak drain current	T_{amb} = 25 °C; single pulse; t_p ≤ 10 µs		-	3.6	A
P_{tot}	total power dissipation	T_{amb} = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T_{sp} = 25 °C		-	2700	mW
T_j	junction temperature			-55	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C
Source-drain diode						
I_S	source current	T_{amb} = 25 °C	[1]	-	670	mA

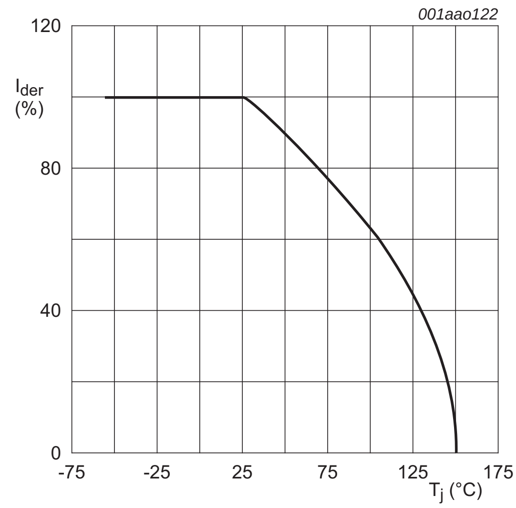
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm^2.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



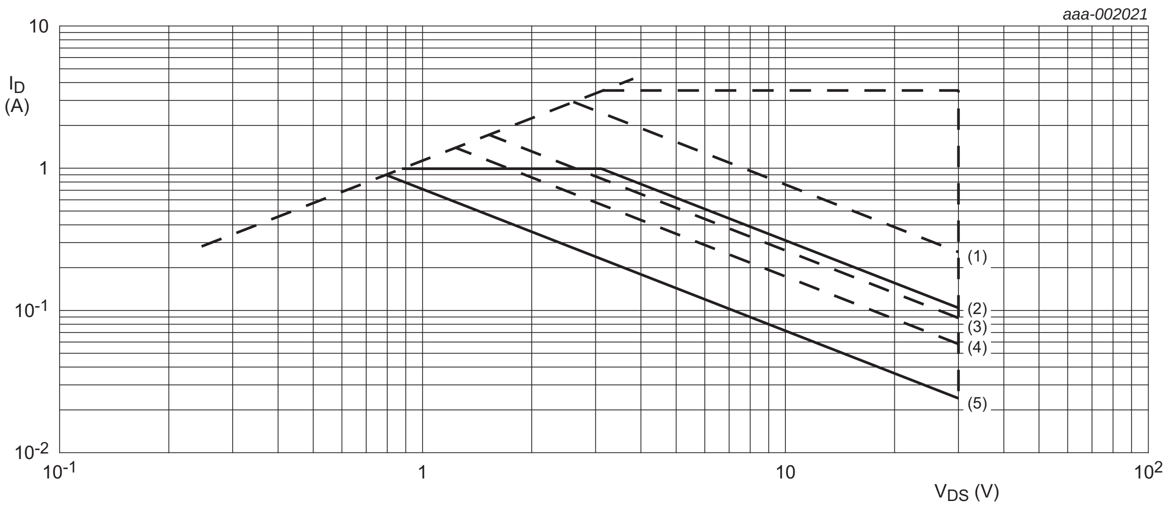
$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of junction temperature



$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\,\%$$

Fig 3. Normalized continuous drain current as a function of junction temperature



I_{DM} is single pulse

(1) t_p = 1 ms

(2) DC; T_{sp} = 25 °C

(3) t_p = 10 ms

(4) t_p = 100 ms

(5) DC; T_{amb} = 25 °C; drain mounting pad 1 cm^2

Fig 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

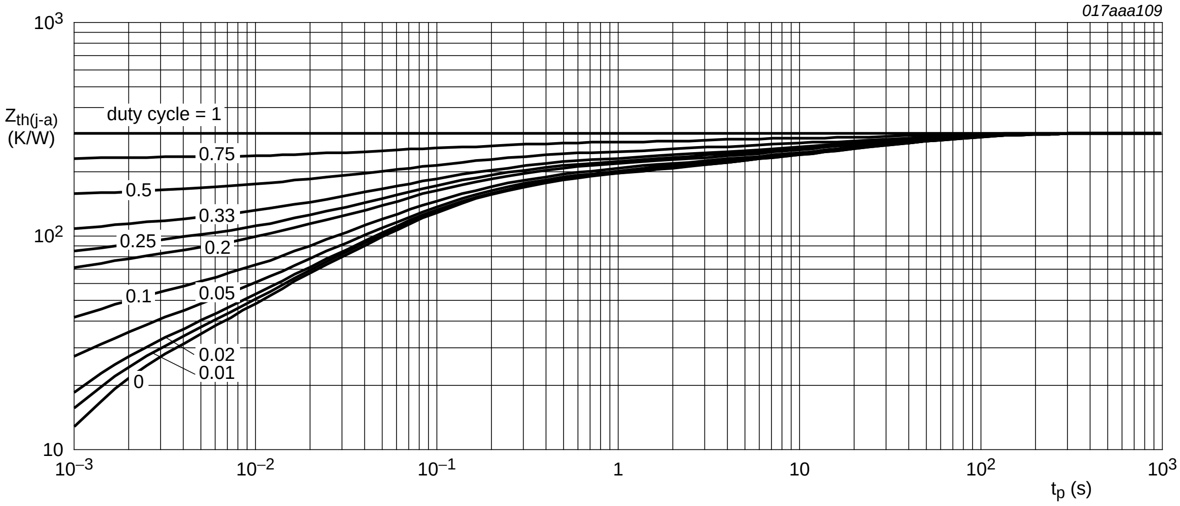
6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	305	360	K/W
			[2]	-	150	175	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	40	K/W

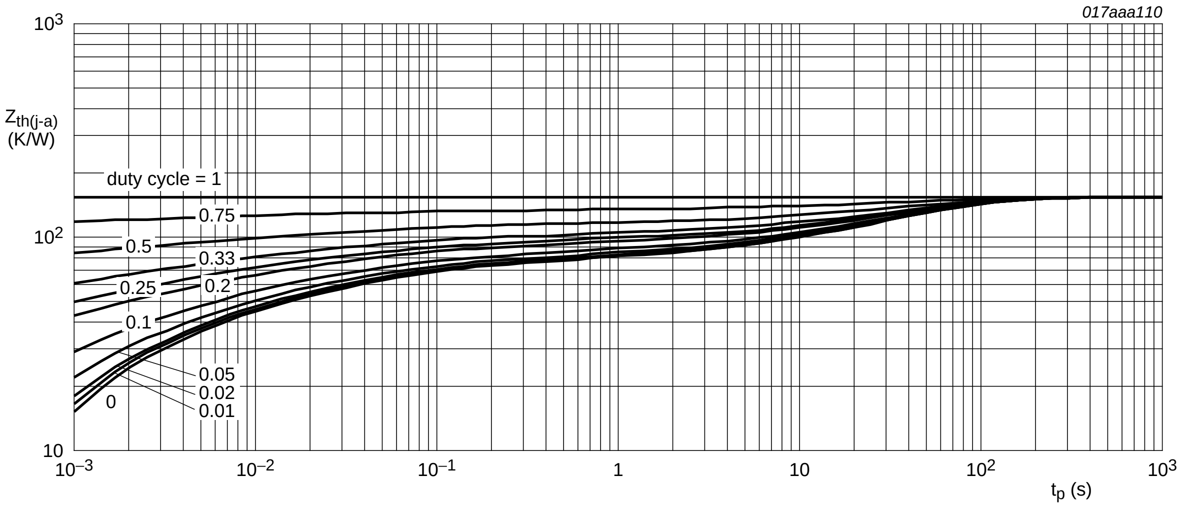
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm^2.



FR4 PCB, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



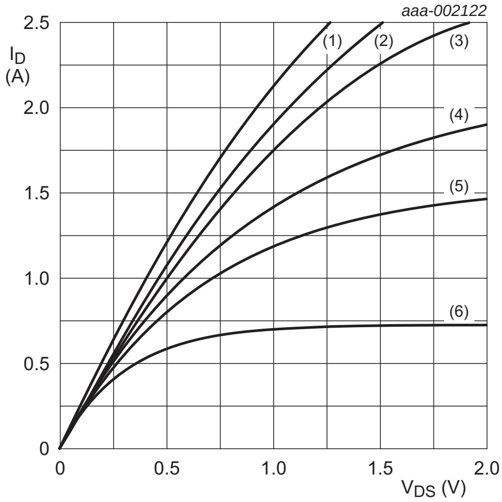
FR4 PCB, mounting pad for drain 1 cm^2

Fig 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

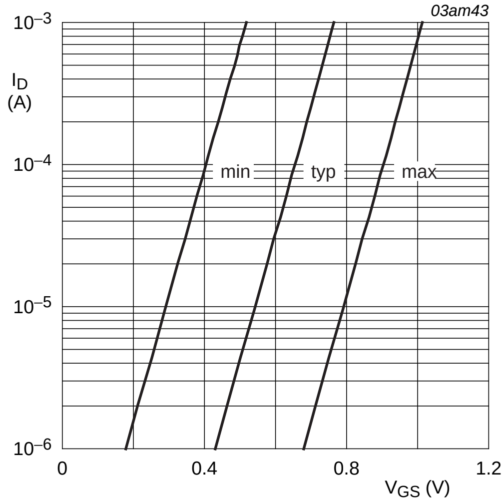
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 10 µA; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS}; T_j = 25 °C	0.45	0.7	0.95	V
I_{DSS}	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	µA
		V_{DS} = 30 V; V_{GS} = 0 V; T_j = 150 °C	-	-	100	µA
I_{GSS}	gate leakage current	V_{GS} = 8 V; V_{DS} = 0 V; T_j = 25 °C	-	-	0.1	µA
		V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 °C	-	-	0.1	µA
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 200 mA; T_j = 25 °C	-	420	490	mΩ
		V_{GS} = 4.5 V; I_D = 200 mA; T_j = 150 °C	-	714	833	mΩ
		V_{GS} = 2.5 V; I_D = 100 mA; T_j = 25 °C	-	490	590	mΩ
		V_{GS} = 1.8 V; I_D = 75 mA; T_j = 25 °C	-	580	760	mΩ
g_{fs}	forward transconductance	V_{DS} = 5 V; I_D = 200 mA; T_j = 25 °C	-	2	-	S
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	V_{DS} = 15 V; I_D = 0.9 A; V_{GS} = 4.5 V; T_j = 25 °C	-	0.75	0.98	nC
Q_{GS}	gate-source charge		-	0.05	-	nC
Q_{GD}	gate-drain charge		-	0.16	-	nC
C_{iss}	input capacitance	V_{DS} = 25 V; f = 1 MHz; V_{GS} = 0 V; T_j = 25 °C	-	43	65	pF
C_{oss}	output capacitance		-	7.7	-	pF
C_{rss}	reverse transfer capacitance		-	4.8	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 15 V; R_L = 15 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 6 Ω; T_j = 25 °C	-	4	8	ns
t_r	rise time		-	7.5	-	ns
$t_{d(off)}$	turn-off delay time		-	18	36	ns
t_f	fall time		-	4.5	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 300 mA; V_{GS} = 0 V; T_j = 25 °C	-	0.76	1.2	V



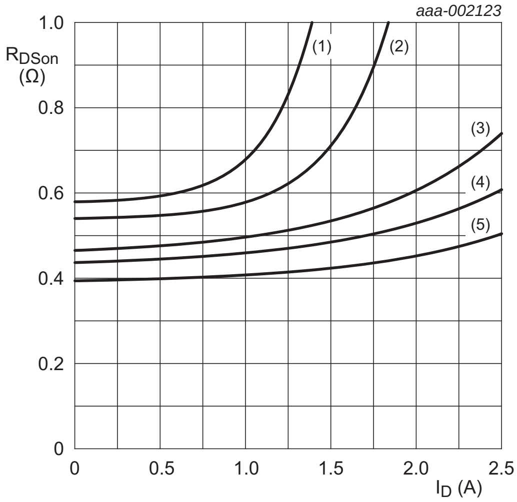
T_j = 25 °C
(1) V_{GS} = 4.5 V
(2) V_{GS} = 3.0 V
(3) V_{GS} = 2.5 V
(4) V_{GS} = 1.8 V
(5) V_{GS} = 1.5 V

Fig 7. Output characteristics: drain current as a function of drain-source voltage; typical values



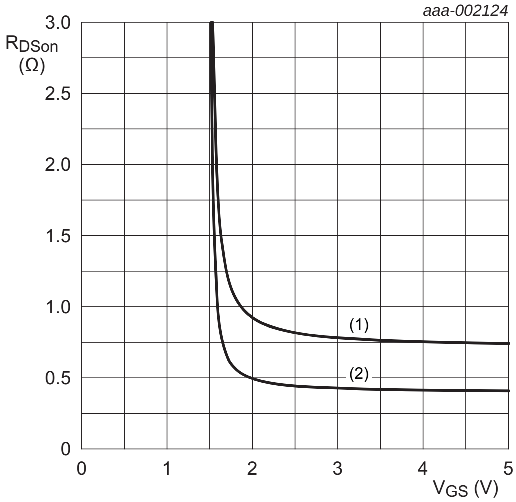
$T_j = 25°C; V_{DS} = 5V$

Fig 8. Subthreshold drain current as a function of gate-source voltage



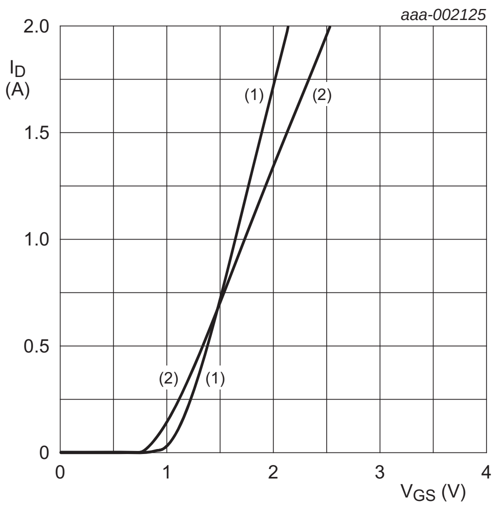
T_j = 25 °C
(1) V_{GS} = 1.8 V
(2) V_{GS} = 2.0 V
(3) V_{GS} = 2.5 V
(4) V_{GS} = 3.0 V
(5) V_{GS} = 4.5 V

Fig 9. Drain-source on-state resistance as a function of drain current; typical values



I_D = 800 mA
(1) T_j = 150 °C
(2) T_j = 25 °C

Fig 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

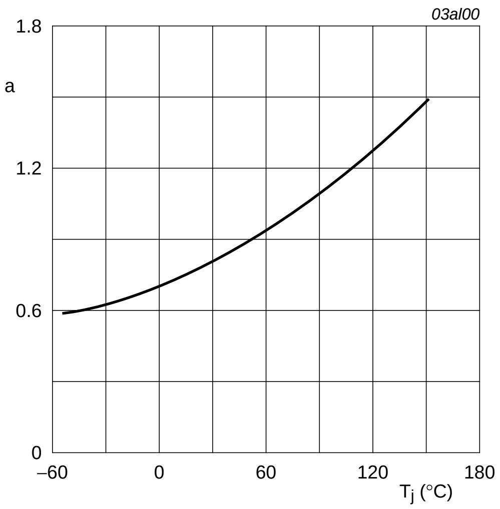


$V_{DS} > I_D \times R_{DSon}$

(1) T_j = 25 °C

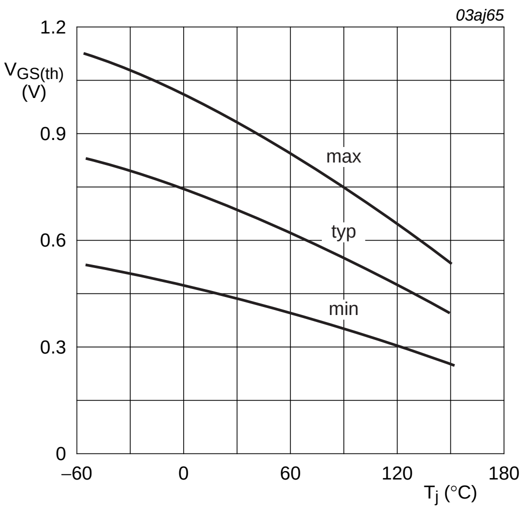
(2) T_j = 150 °C

Fig 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values



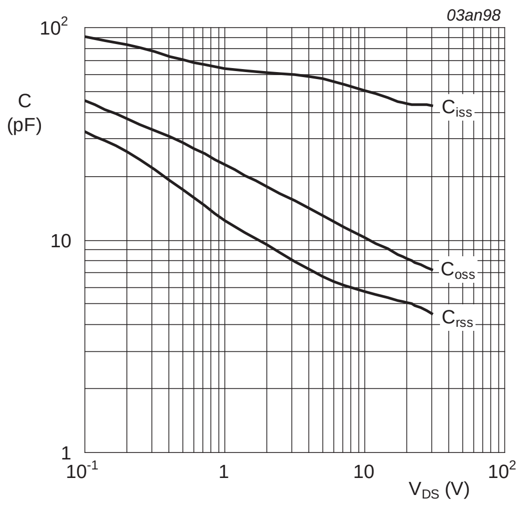
$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



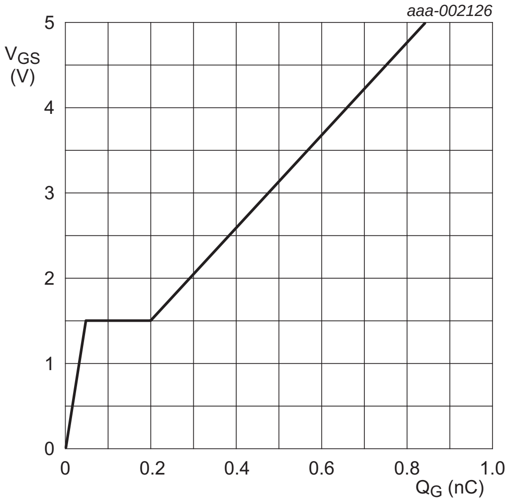
I_D = 0.25 mA; $V_{DS} = V_{GS}$

Fig 13. Gate-source threshold voltage as a function of junction temperature



$$V_{GS} = 0V; f = 1MHz$$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



I_D = 900 mA; V_{DS} = 15 V; T_{amb} = 25 °C

Fig 15. Gate-source voltage as a function of gate charge; typical values

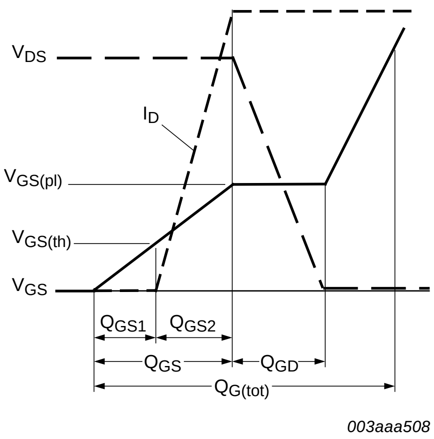
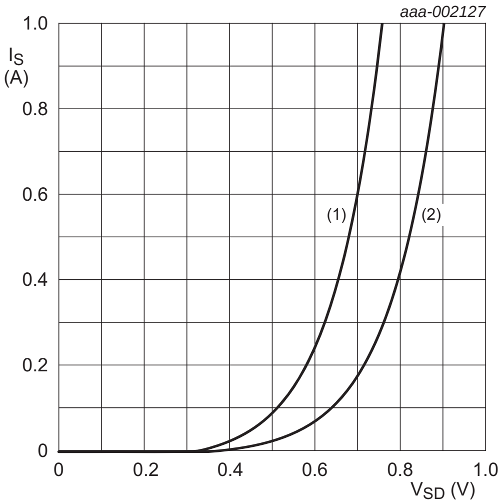


Fig 16. Gate charge waveform definitions



V_{GS} = 0 V

(1) T_j = 150 °C

(2) T_j = 25 °C

Fig 17. Source current as a function of source-drain voltage; typical values

8. Test information

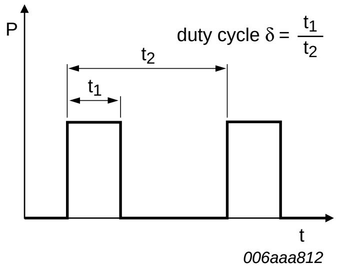


Fig 18. Duty cycle definition

9. Package outline

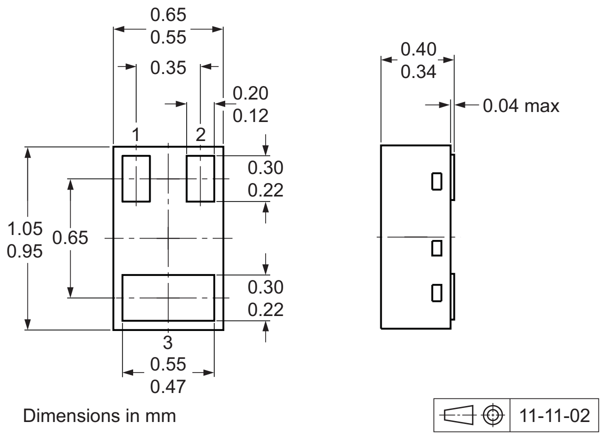


Fig 19. Package outline SOT883B (DFN1006B-3)

10. Soldering

Footprint information for reflow soldering SOT883B

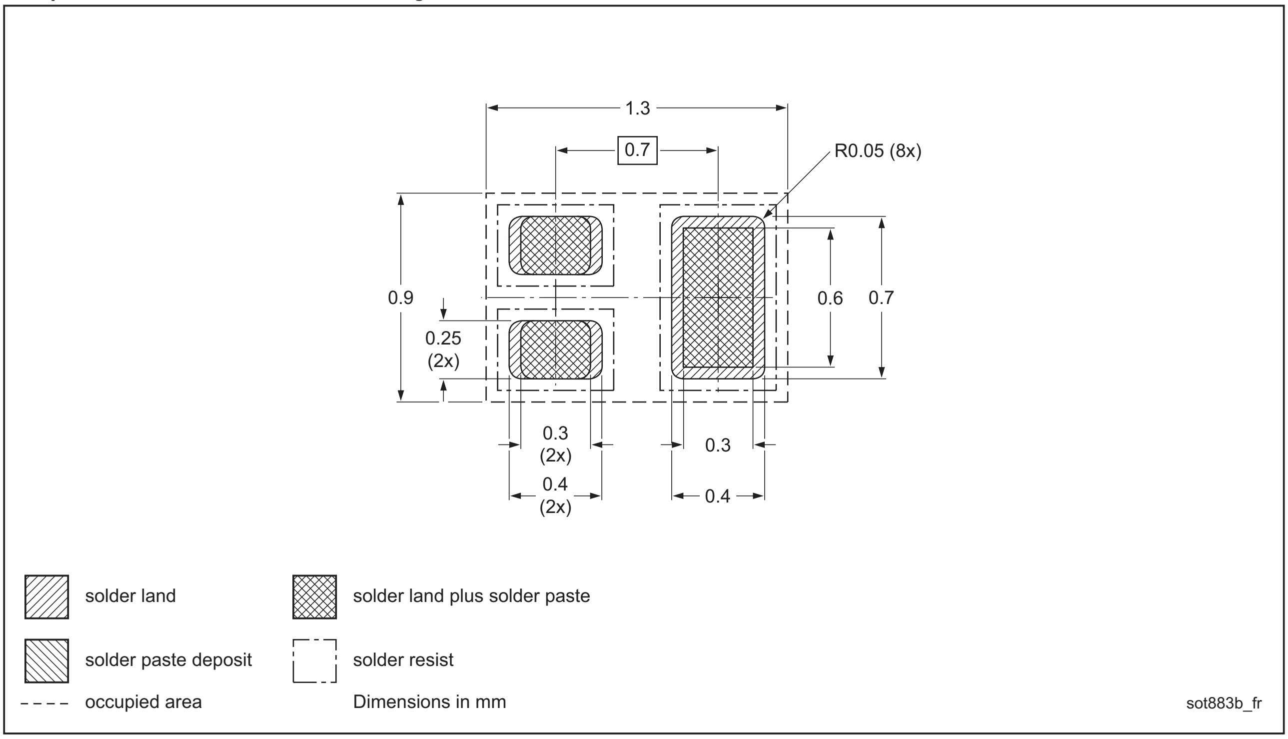


Fig 20. Reflow soldering footprint for SOT883B (DFN1006B-3)

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMZB420UN v.1	20120511	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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14. Contents

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